

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVV020** is Designed for

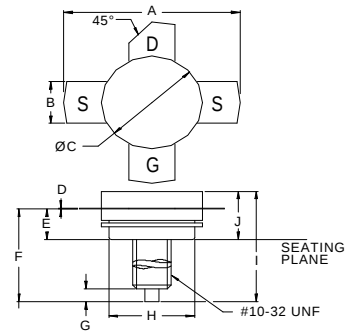
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CEO}	35 V
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	140 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	1.5°C/W

PACKAGE STYLE .500 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.050 / 26.67
B	.220 / 5.59	.230 / 5.84
C	.495 / 12.57	.505 / 12.83
D	.003 / 0.08	.007 / 0.18
E	.160 / 4.06	.180 / 4.57
F	.622 / 15.80	
G	.100 / 2.54	.130 / 3.31
H	.415 / 10.54	.425 / 10.80
I	.720 / 18.29	
J	.250 / 6.35	.290 / 7.37

ORDER CODE: ASI10659

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 50\text{ mA}$	65			V
BV_{CER}	$I_C = 50\text{ mA}$ $R_{BE} = 10\ \Omega$	60			V
BV_{CEO}	$I_C = 50\text{ mA}$	35			V
BV_{EBO}	$I_E = 10\text{ mA}$	4.0			V
I_{CES}	$V_{CB} = 50\text{ V}$			5.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	20		120	---
C_{OB}	$V_{CB} = 30\text{ V}$ $f = 1.0\text{ MHz}$			85	pF
P_G	$V_{CE} = 25\text{ V}$ $I_C = 2.5\text{ A}$ $f = 225\text{ MHz}$	8.0			dB
IMD_3	$P_{OUT} = 14\text{ W}$	-51			dBc